

**Vishay Semiconductors** 

## HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 8 A





PRODUCT SUMMARY									
Package	TO-220AC								
I <sub>F(AV)</sub>	8 A								
V <sub>R</sub>	600 V								
V <sub>F</sub> at I <sub>F</sub>	1.4 V								
t <sub>rr</sub> typ.	18 ns								
T <sub>J</sub> max.	150 °C								
Diode variation	Single die								

### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION

VS-HFA08TB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB60 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		600	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8						
Single pulse forward current	I <sub>FSM</sub>		60	А					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum namer dissinction	Р	T <sub>C</sub> = 25 °C	36	10/					
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	14	W					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					

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RoHS

COMPLIANT

HALOGEN

FREE



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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-			
		I <sub>F</sub> = 8.0 A		-	1.4	1.7	V		
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A	See fig. 1	-	1.7	2.1			
		$I_F = 8.0 \text{ A}, T_J = 125 \text{ °C}$		-	1.4	1.7			
Maximum reverse		$V_R = V_R$ rated	See fig. 2	-	0.3	5.0			
leakage current	I <sub>RM</sub>	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	100	500	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	10	25	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ c}$	A/μs, V <sub>R</sub> = 30 V	-	18	-	ns			
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	37	55				
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	55	90				
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	3.5	5.0	A			
Feak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8.0 A dI <sub>F</sub> /dt = 200 A/μs	-	4.5	8.0				
Poveres resource abarga	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{\rm B} = 200 \text{ V}$	-	65	138				
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	124	360	ne			
Peak rate of fall of recovery	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C	]	-	240	-	A /			
current during t <sub>b</sub>	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	210	-	A∕µs			

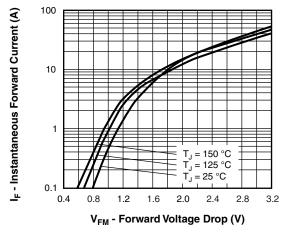
THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C					
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	3.5						
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W					
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-						
Waight			-	2.0	-	g					
Weight			-	0.07	-	oz.					
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)					
Marking device		Case style TO-220AC		HFA0	8TB60						

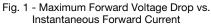
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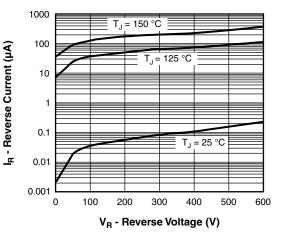
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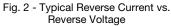


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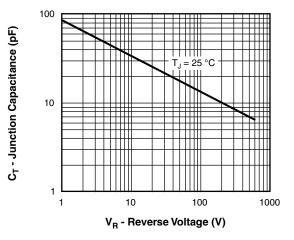
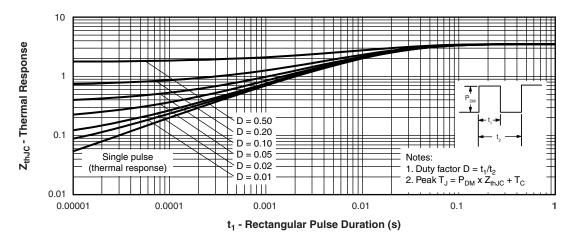


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

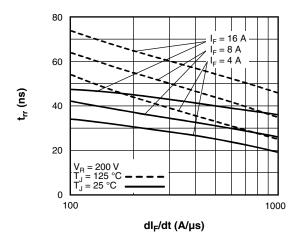




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Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

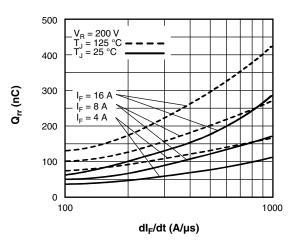


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

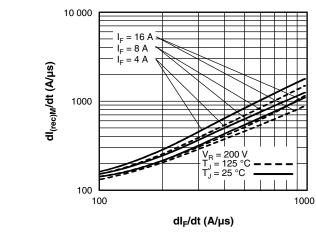


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

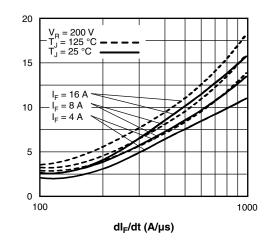


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt

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I<sub>rr</sub> (A)

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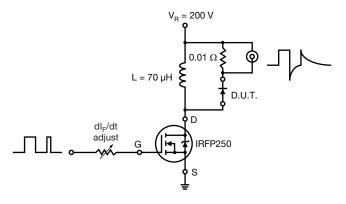


Fig. 9 - - Reverse Recovery Parameter Test Circuit

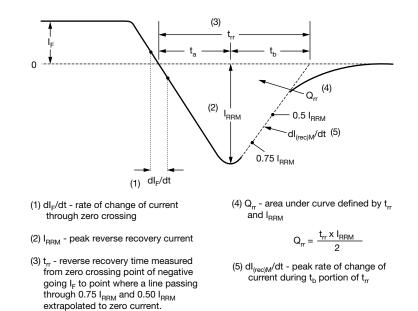


Fig. 10 - Reverse Recovery Waveform and Definitions



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#### **ORDERING INFORMATION TABLE**

Device code	vs-	HF	Α	08	тв	60	PbF
	1	2	3	4	5	6	7
	1 - 2 - 3 - 4 - 5 -	HEX Elec Cur Pac	KFRED <sup>®</sup>	adiated ng (08 =	·	oduct	
	6 - 7 -	Volt	age rati	ng (60 = ntal digit	,		
				(Pb)-fre jen-free,			-

ORDERING INFORMATION (Example)									
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION									
VS-HFA08TB60PbF	50	1000	Antistatic plastic tube						
VS-HFA08TB60-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95221						
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224						
	TO-220AC-N3	www.vishay.com/doc?95068						



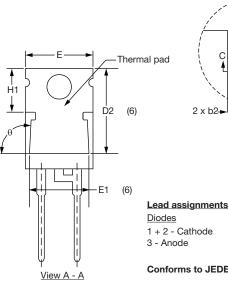
**Vishay Semiconductors** 

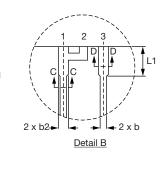
**TO-220AC** 

plane

#### **DIMENSIONS** in millimeters and inches









**Diodes** 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIN	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	OTMEDEL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimension: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1
- <sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- <sup>(8)</sup> Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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